JCT810H 10A SCR

Rev.A.1.1

DESCRIPTION:

Average gate power dissipation (T_j=125)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W

Peak pulse voltage
(T_j=25 ; non-repetitive,0 152.526i gate power

ORDERING INFORMATION

J	CT	8	10	H
JieJie Microelectronics Co., Ltd.	SCRs	8:V_{DRM} /V_{RRM} 1800 V	$I_{T(RMS)}$:10A	H:TO-251

MARKING

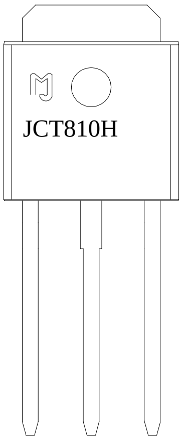
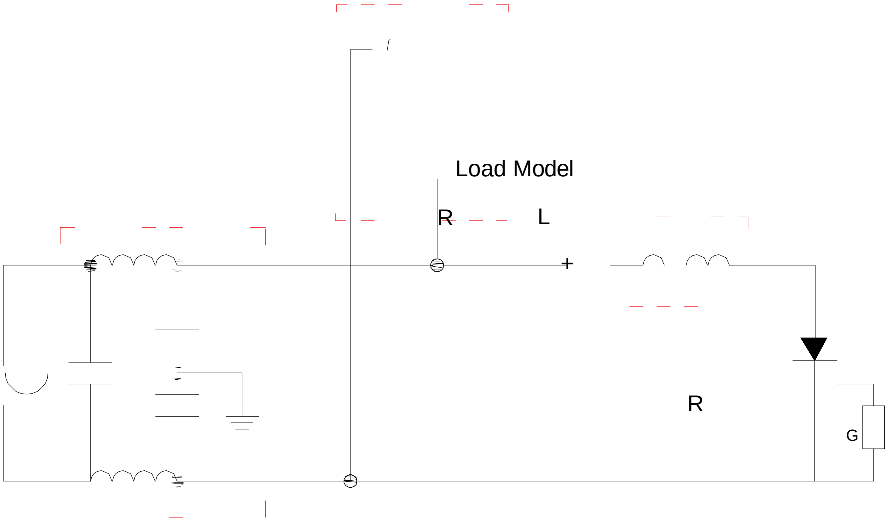


FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards.



ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package

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